



Description

JMT N-channel Enhancement Mode Power MOSFET

Features

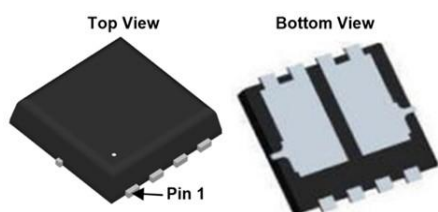
- 30V, 15A
 $R_{DS(ON)} < 14m\Omega$ @ $V_{GS} = 10V$
 $R_{DS(ON)} < 25m\Omega$ @ $V_{GS} = 4.5V$
- Advanced Trench Technology
- Provide Excellent $R_{DS(ON)}$ and Low Gate Charge
- Lead free product is acquired

Application

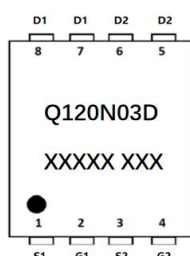
- Load Switch
- PWM Application
- Power management



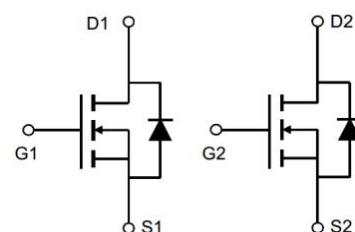
100% UIS TESTED!
100% ΔV_{ds} TESTED!



PDFN3x3-8L-D



Marking and pin Assignment



Schematic Diagram

Package Marking and Ordering Information

Device Marking	Device	OUTLINE	Device Package	Reel Size	Reel (PCS)	Per Carton (PCS)
Q120N03D	JMTQ120N03D	TAPING	PDFN3x3-8L-D	13inch	5000	50000

Absolute Maximum Ratings ($T_C = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter		Max.	Units
V _{DSS}	Drain-Source Voltage		30	V
V _{GSS}	Gate-Source Voltage		±20	V
I _D	Continuous Drain Current	T _C = 25°C	15	A
		T _C = 100°C	9.8	A
I _{DM}	Pulsed Drain Current ^{note1}		60	A
E _{AS}	Single Pulsed Avalanche Energy ^{note2}		12	mJ
P _D	Power Dissipation	T _C = 25°C	5.4	W
R _{θJC}	Thermal Resistance, Junction to Case		23	°C/W
T _J , T _{STG}	Operating and Storage Temperature Range		-55 to +150	°C



Electrical Characteristics (T_J=25°C unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	30	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =30V, V _{GS} =0V,	-	-	1.0	μA
I _{GSS}	Gate to Body Leakage Current	V _{DS} =0V, V _{GS} =±20V	-	-	±100	nA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	1.0	1.5	2.5	V
R _{DS(on)}	Static Drain-Source on-Resistance note3	V _{GS} =10V, I _D =10A	-	11	14	mΩ
		V _{GS} =4.5V, I _D =5A	-	18	25	
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} =15V, V _{GS} =0V, f=1.0MHz	-	614	-	pF
C _{Oss}	Output Capacitance		-	118	-	pF
C _{rss}	Reverse Transfer Capacitance		-	98	-	pF
Q _g	Total Gate Charge	V _{DS} =15V, I _D =11A, V _{GS} =10V	-	16	-	nC
Q _{gs}	Gate-Source Charge		-	2.7	-	nC
Q _{gd}	Gate-Drain(“Miller”) Charge		-	4.5	-	nC
Switching Characteristics						
t _{d(on)}	Turn-on Delay Time	V _{DS} =15V,R _L =1.35Ω, R _{GEN} =3Ω, V _{GS} =10V	-	6	-	ns
t _r	Turn-on Rise Time		-	10	-	ns
t _{d(off)}	Turn-off Delay Time		-	30	-	ns
t _f	Turn-off Fall Time		-	6.5	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I _S	Maximum Continuous Drain to Source Diode Forward Current		-	-	15	A
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	60	A
V _{SD}	Drain to Source Diode Forward Voltage	V _{GS} =0V, I _S =15A	-	-	1.2	V
t _{rr}	Body Diode Reverse Recovery Time	I _F =11A,dI/dt=500A/μs	-	7	-	ns
Q _{rr}	Body Diode Reverse Recovery Charge		-	10	-	nC

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. EAS condition: T_J=25°C, V_{GS}=15V, R_G=25Ω, L=0.5mH, I_{AS}=7A

3. Pulse Test: Pulse Width≤300μs, Duty Cycle≤0.5%



Typical Performance Characteristics

Figure1: Output Characteristics

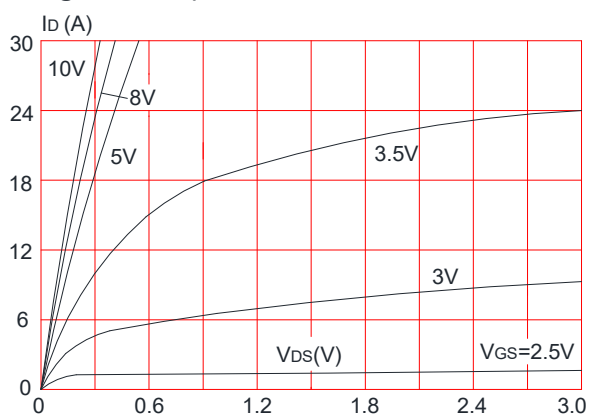


Figure 2: Typical Transfer Characteristics

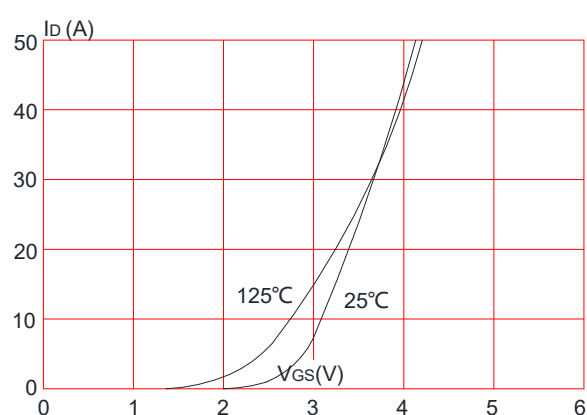


Figure 3: On-resistance vs. Drain Current

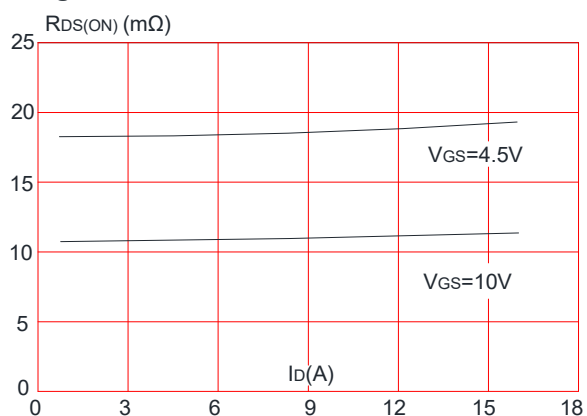


Figure 4: Body Diode Characteristics

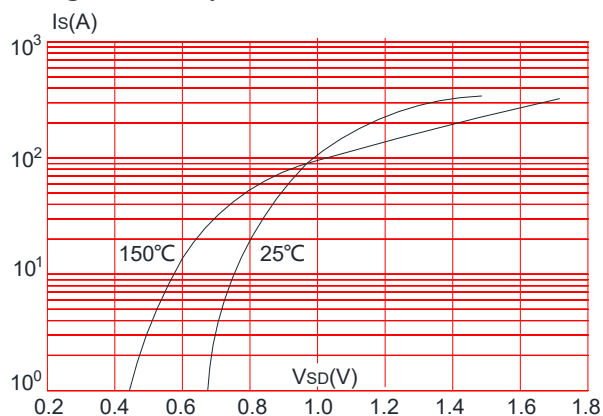


Figure 5: Gate Charge Characteristics

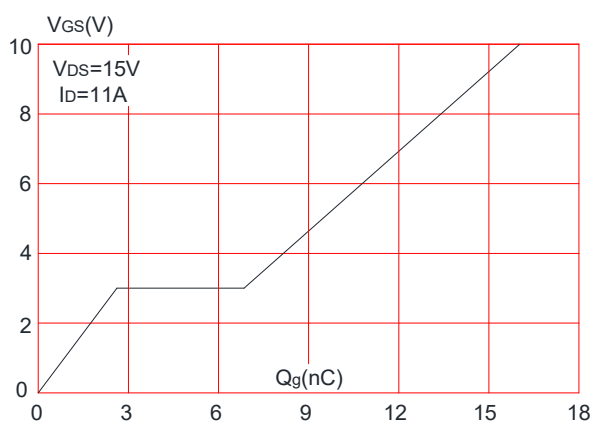


Figure 6: Capacitance Characteristics

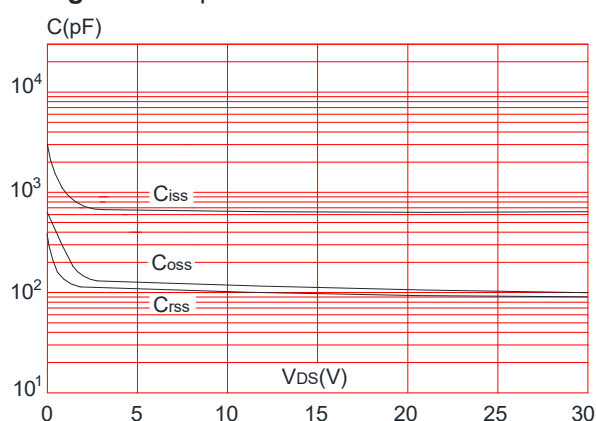


Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

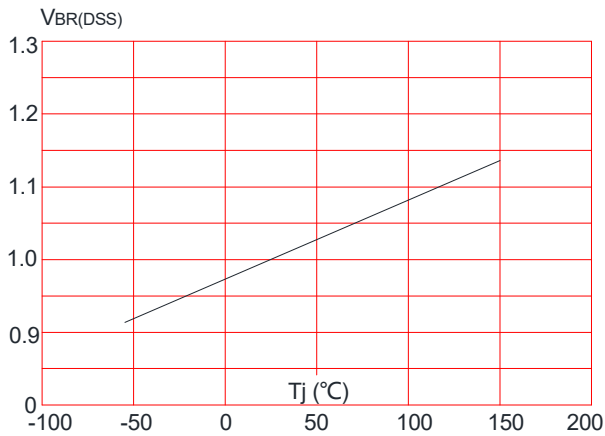


Figure 8: Normalized on Resistance vs. Junction Temperature

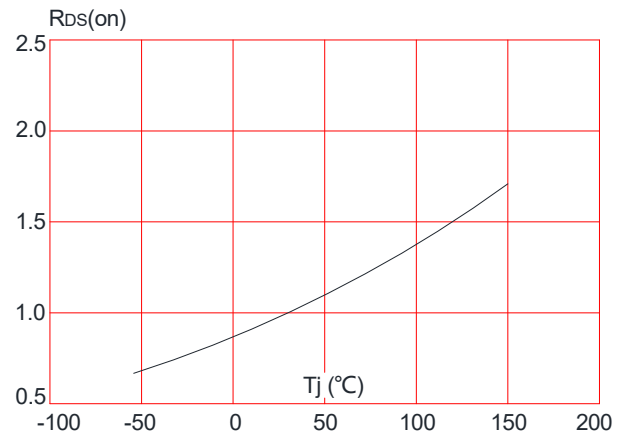


Figure 9: Maximum Safe Operating Area

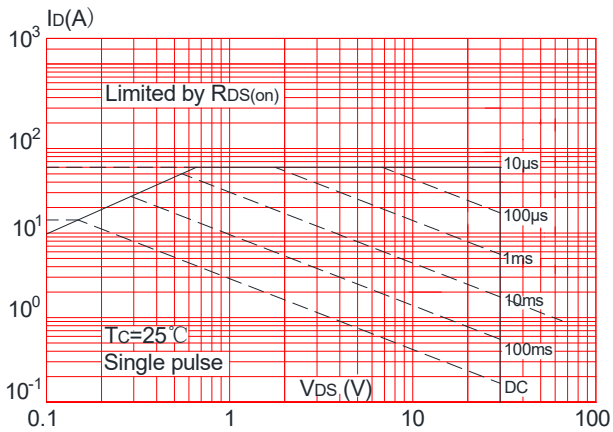


Figure 10: Maximum Continuous Drain Current vs. Case Temperature

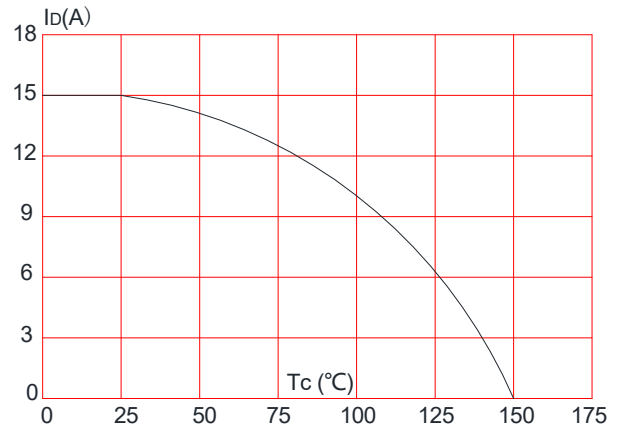
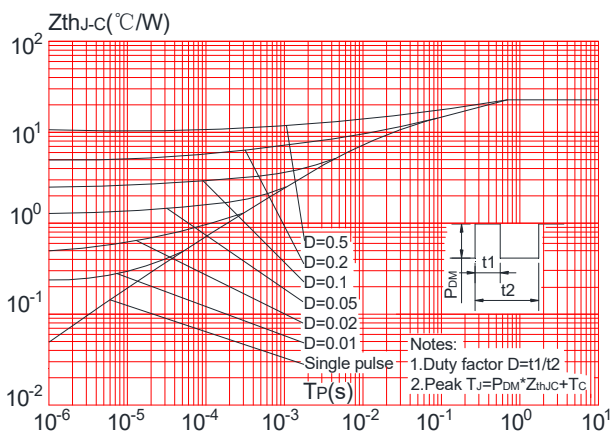


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Case



Test Circuit

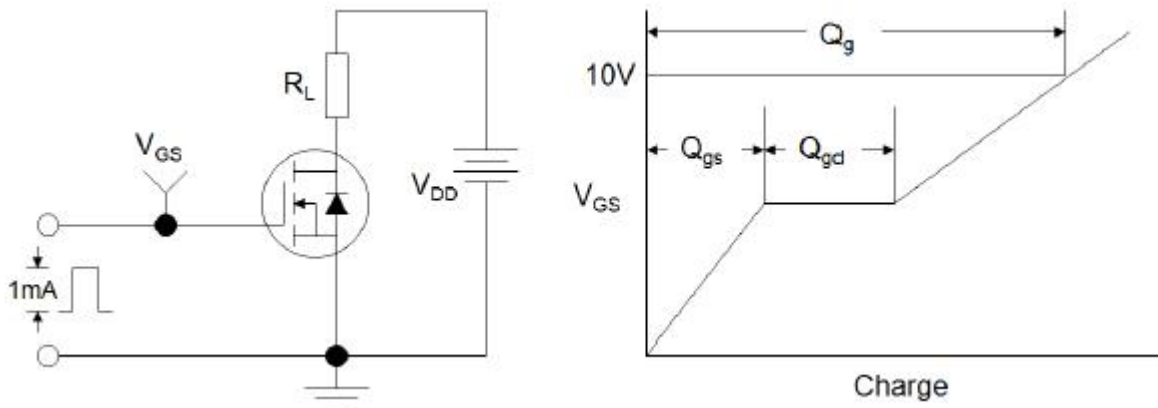


Figure1:Gate Charge Test Circuit & Waveform

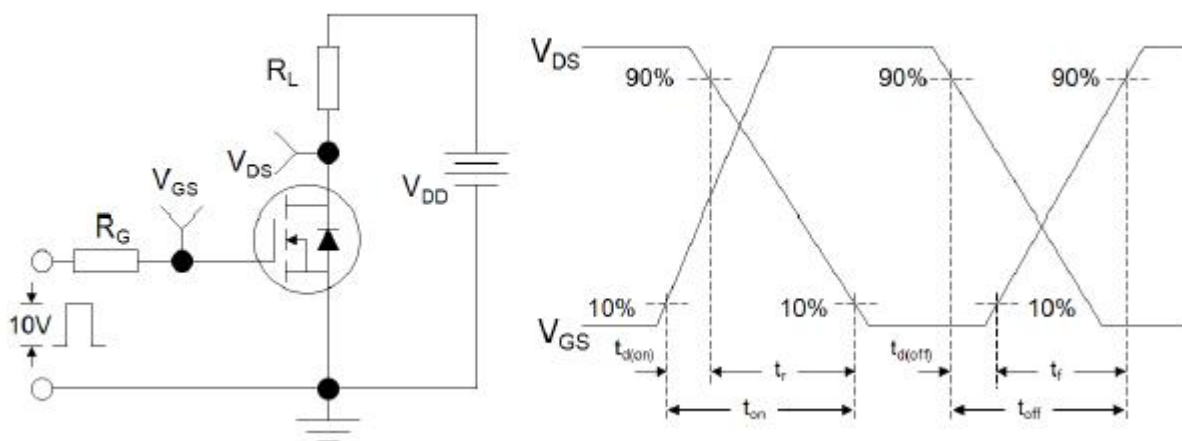


Figure 2: Resistive Switching Test Circuit & Waveforms

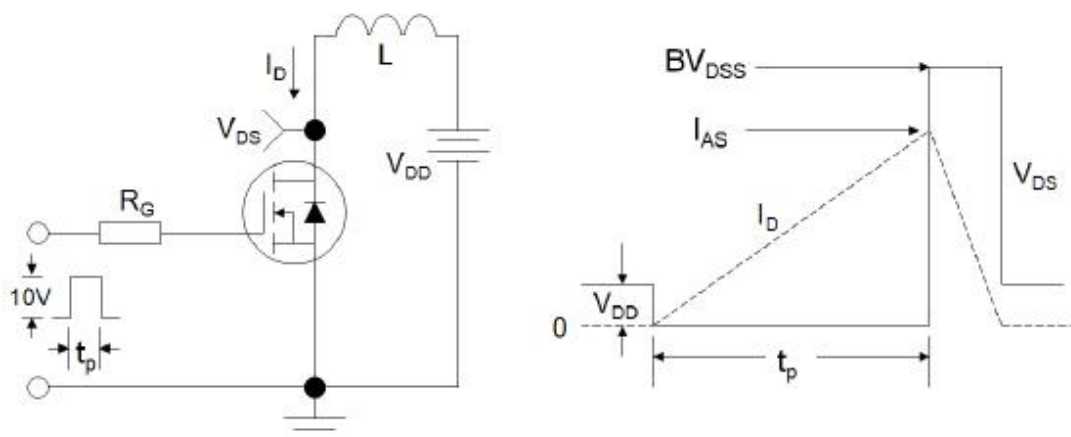
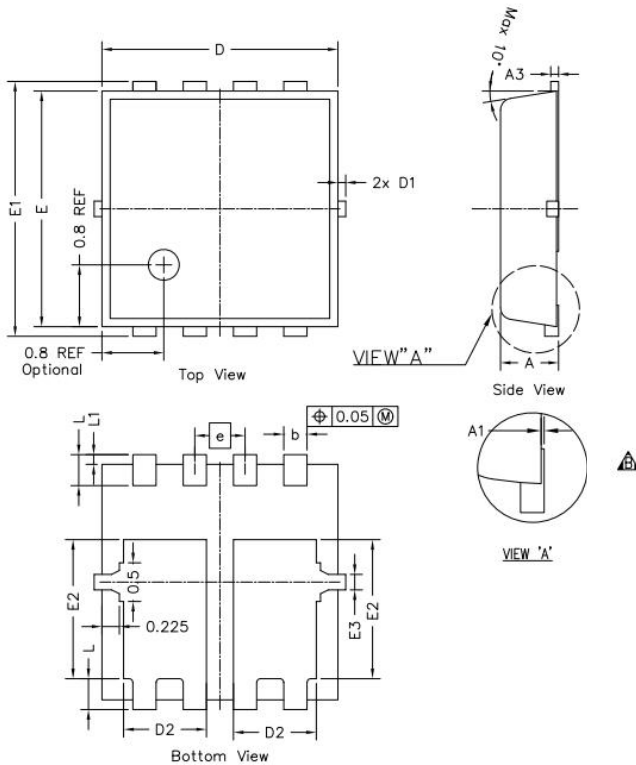


Figure 3:Unclamped Inductive Switching Test Circuit & Waveforms



Package Mechanical Data-PDFN3x3-8L-D



SYMBOLS	DIMENSION IN MM			DIMENSION IN INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.700	0.750	0.800	0.028	0.030	0.031
A1	---	---	0.050	----	----	0.002
A3	0.144	0.152	0.202	0.006	0.006	0.008
b	0.250	0.300	0.350	0.010	0.012	0.014
e	0.65 BSC			0.026 BSC		
D	2.950	3.050	3.150	0.116	0.120	0.124
E	2.950	3.050	3.150	0.116	0.120	0.124
D1	---	---	0.125	----	----	0.005
E1	3.200	3.300	3.400	0.126	0.130	0.134
D2	0.970	1.070	1.170	0.038	0.042	0.046
E2	1.700	1.800	1.900	0.067	0.071	0.075
E3	0.150	0.200	0.250	0.006	0.008	0.010
L	0.300	0.400	0.500	0.012	0.016	0.020
L1	0.075	0.125	0.175	0.003	0.005	0.007

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